



TRANSMITTAL LETTER
(General - Patent Pending)

Docket No.
PHUS010631

In Re Application Of: **Letavic et al.**

Serial No.
10/015,640

Filing Date
12/10/2001

Examiner
Ngo, N.

Group Art Unit
2814

Title: **HIGH FREQUENCY HIGH VOLTAGE SILICON-ON-INSULATOR DEVICE WITH MASK VARIABLE
INVERSION CHANNEL AND METHOD FOR FORMING THE SAME**

TO THE ASSISTANT COMMISSIONER FOR PATENTS:


Transmitted herewith is: **Amendment in 4 pages**

Separate Markup Sheet in 2 pages
2 Return Receipt Postcards

in the above identified application.

- ☒ No additional fee is required.
- ☐ A check in the amount of _____ is attached.
- ☒ The Assistant Commissioner is hereby authorized to charge and credit Deposit Account No. **500999**
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- ☐ Charge the amount of _____
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Signature

Dated: **November 25, 2002**

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I certify that this document and fee is being deposited
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20231.



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Dorothea Rubbone

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CC:



DOCKET NO. PHUS010631

2814
#1/B
Amend 13
y/Johnson
12/13/02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Letavic et al.)	Examiner: Ngo, N.
)	
Application No.: 10/015,640)	Art Unit: 2814
)	
Filed: 12/10/2001)	
)	
For: HIGH FREQUENCY HIGH VOLTAGE)	
SILICON-ON-INSULATOR DEVICE WITH)	
MASK VARIABLE INVERSION CHANNEL)	
AND METHOD FOR FORMING THE SAME)	

Commissioner for Patents
Washington D.C. 20231

AMENDMENT

Sir:

In response to the Office Action of September 10, 2002, please amend the application as follows:

In the Claims

Claims 1 and 8 have been amended as follows as indicted in the attached Separate

Markup Sheet:

1. (Amended) A high frequency semiconductor device having a shifted doping profile,
comprising:

B) a buried oxide layer formed over a semiconductor substrate; and

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